

**Silicon PNP Power Transistor**

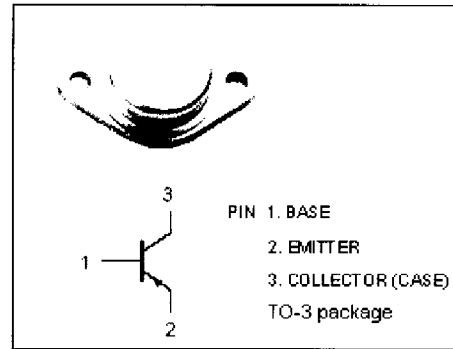
**2SA651**

**DESCRIPTION**

- Collector-Emitter Breakdown Voltage-  
 :  $V_{(BR)CEO} = -150V(\text{Min.})$
- Wide Area of Safe Operation

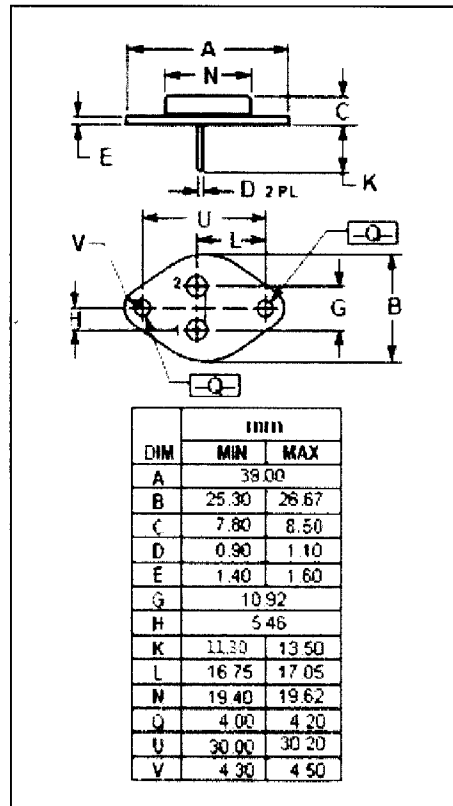
**APPLICATIONS**

- Designed for audio power amplifier applications.

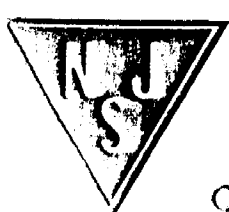


**ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-200	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_c$	Collector Current-Continuous	-10	A
$P_c$	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	100	W
$T_j$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature	-55~150	$^\circ\text{C}$



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# Silicon PNP Power Transistor

2SA651

## ELECTRICAL CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>E</sub> = 0	-200			
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -25mA; I <sub>B</sub> = 0	-150			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -1mA; I <sub>C</sub> = 0	-5			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-2.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -5A; I <sub>B</sub> = -0.5A			-2.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -200V; I <sub>E</sub> = 0			-0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -5V; I <sub>C</sub> = 0			-0.1	mA
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -2A; V <sub>CE</sub> = -5V	30		150	
C <sub>OB</sub>	Collector Output Capacitance	I <sub>E</sub> =0; V <sub>CB</sub> = -5V; f= 1MHz		500		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -10V		10		MHz